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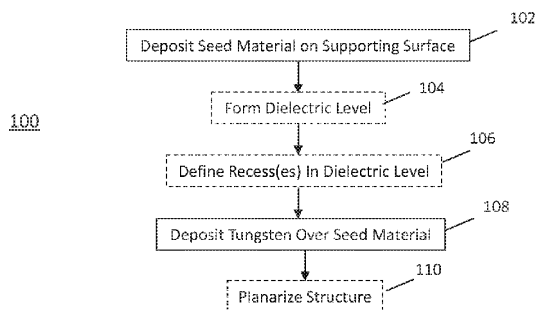


FIG. 1

(57) Abstract: Described are methods for forming a multilayer
conductive structure for semiconductor devices. A seed layer is
formed comprising a metal and an additional constituent that in
combination with the metal inhibits nucleation of a fill layer of
the metal formed over the seed layer. Tungsten may be doped or
alloyed with silicon to form the seed layer, with a tungsten fill
being formed over the seed layer.